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|--|-------------|-----|----|
| Average gate power dissipation ($T_j=125$) | $P_{G(AV)}$ | 0.5 | W |
| Peak gate power | P_{GM} | 10 | W |
| Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7) | V_{pp} | 3.5 | kV |

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

| Symbol | Test Condition | Quadrant | Value | | Unit |
|----------|--------------------|----------|-------|----|------|
| I_{GT} | $V_D=12V$ $R_L=33$ | - - | MAX. | 10 | mA |
| V_{GT} | | - - | MAX. | 1 | V |

 V_{GD}

ORDERING INFORMATION

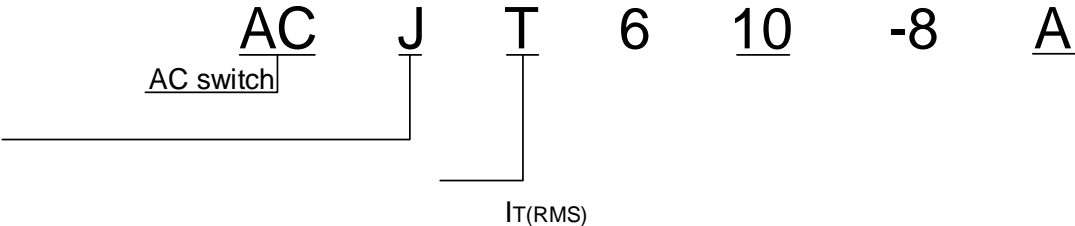


FIG.1: Maximum power dissipation versus RMS on-state current

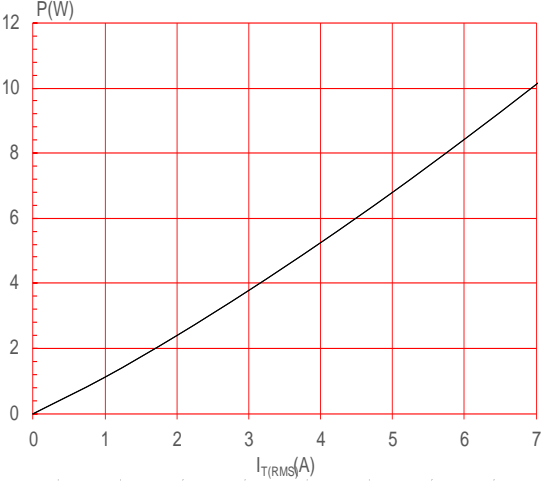
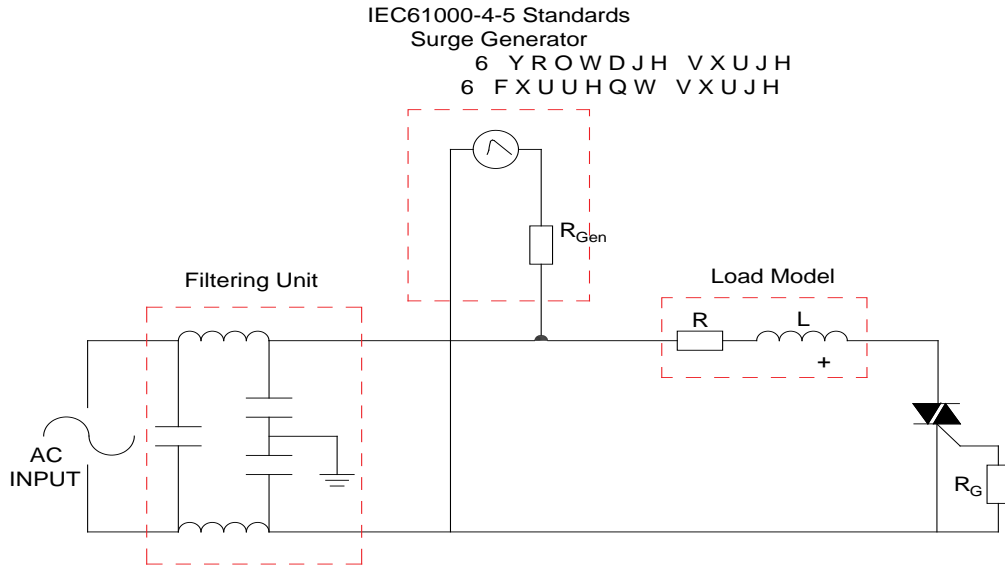


FIG.2: RMS on-state current versus case temperature


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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